Electronic Supplementary Material (ESI) for RSC Advances.

First-principles study of thermoelectric properties of Mg_2Si-Mg_2Pb semiconductor materials

Tao Fan,*[ab] Congwei Xie,[ac] Shiyao Wang,[a] Artem R. Oganov*[acd] and Laifei Cheng[b]

[a.] *International Center for Materials Discovery, School of Materials Science and Engineering, Northwestern Polytechnical University, Xi'an, Shaanxi 710072, P. R. China. E-mail: nwpufant@mail.nwpu.edu.cn*

[b.] *Science and Technology on Thermostructural Composite Materials Laboratory, School of Materials Science and Engineering, Northwestern Polytechnical University, Xi'an, Shaanxi 710072, P. R. China.*

[c.] *Skolkovo Innovation Center, Skolkovo Institute of Science and Technology, Moscow 143026, Russia. E-mail: A.Oganov@skoltech.ru*

[d.] *Moscow Institute of Physics and Technology, 9 Institutskiy Lane, Dolgoprudny City, Moscow Region 141700, Russia*

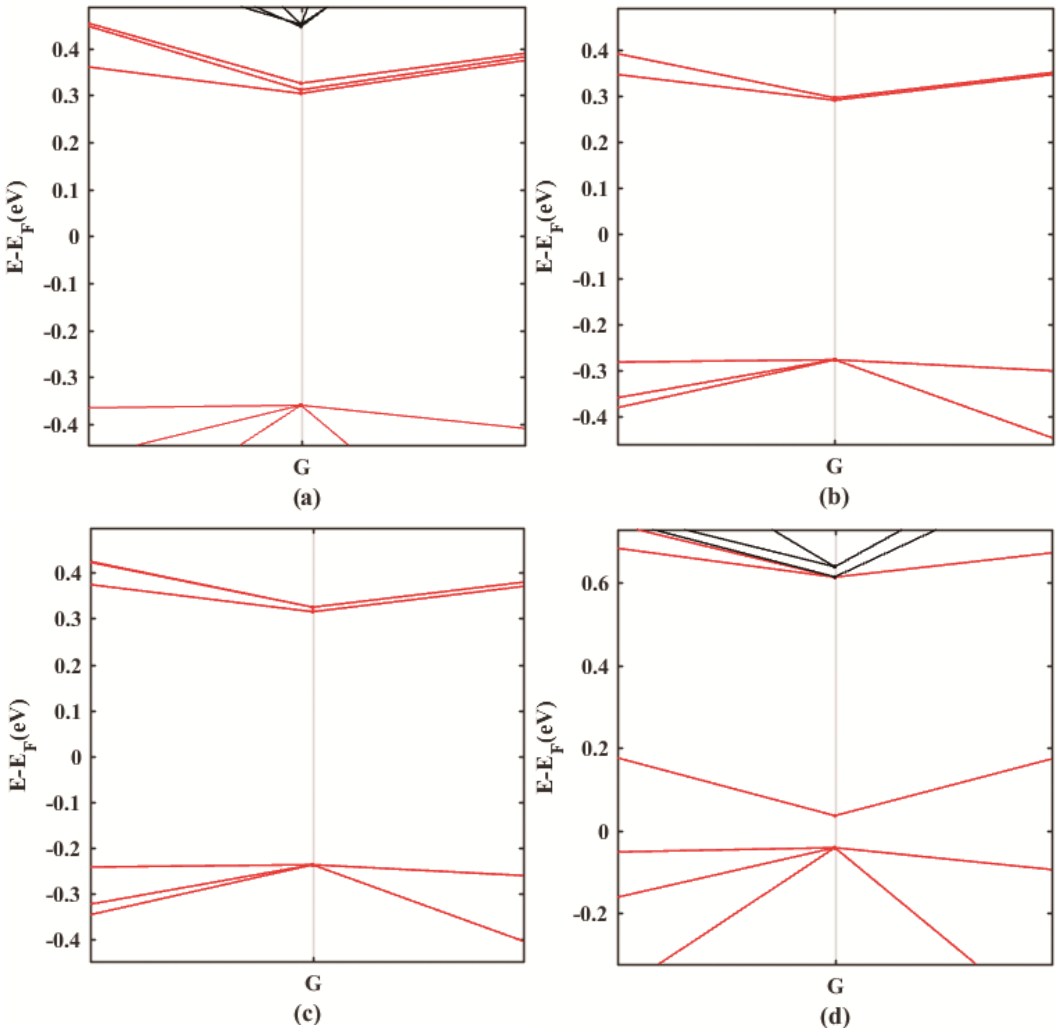

Fig. S1 Enlarged drawings of band structure near band gap. (a) Mg_2Si; (b) $Mg_{64}Si_{31}Pb$; (c) $Mg_{64}Si_{30}Pb_2$; (d) Mg_8Si_3Pb. In each figure, the Fermi level E_F was shifted to zero.

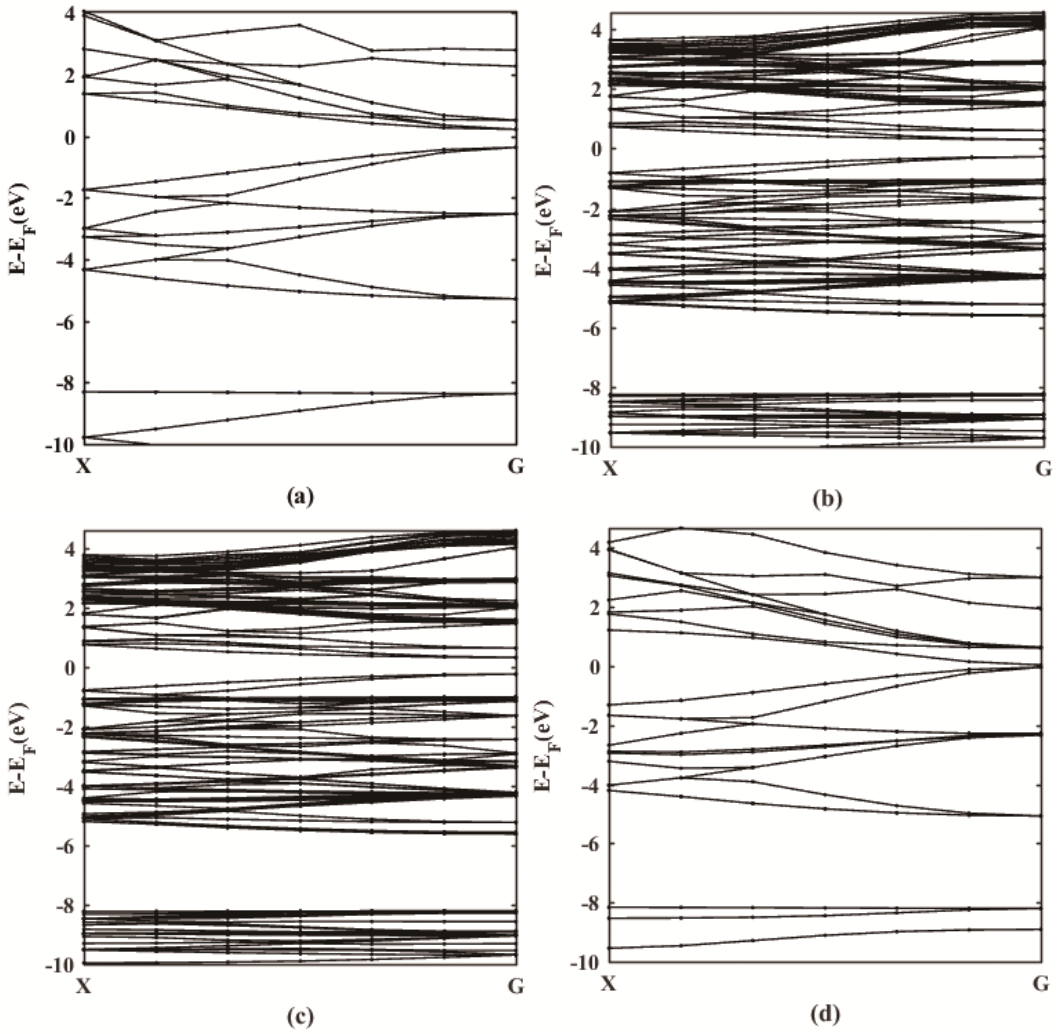

Fig. S2 Band structures along X-G path. (a) Mg_2Si; (b) $Mg_{64}Si_{31}Pb$; (c) $Mg_{64}Si_{30}Pb_2$; (d) Mg_8Si_3Pb. In each figure, the Fermi level E_F was shifted to zero.